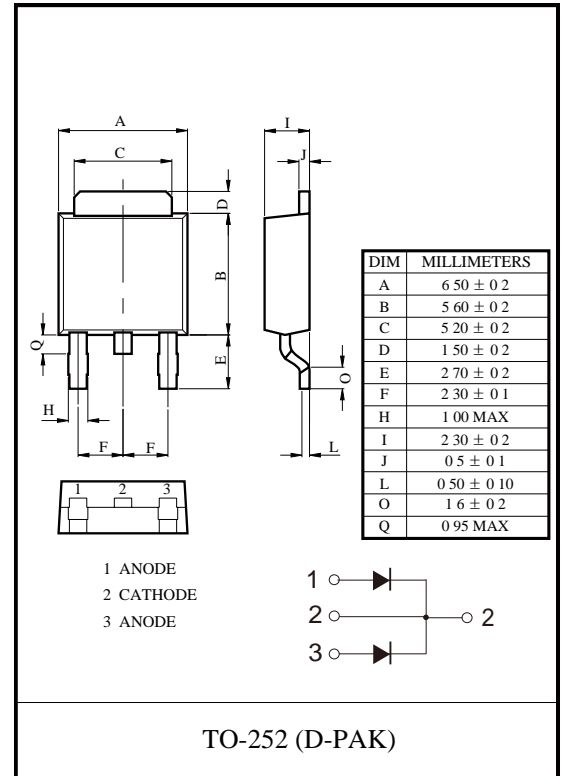


MBRD20100CT SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{RRM}	Peak repetitive reverse voltage	100	V
V _{RWM}	Working peak reverse voltage		
V _{R(RMS)}	RMS reverse voltage	70	V
I _O	Average rectified output current	20	A
I _{FSM}	Non-repetitive peak forward surge current 8.3ms half sine wave	120	A
R _{ΘJA}	Thermal resistance from junction to ambient (note : Test with 2inch Al board)	100	°C/W
T _j	Junction temperature	150	°C
T _{stg}	Storage temperature	-55~+150	°C

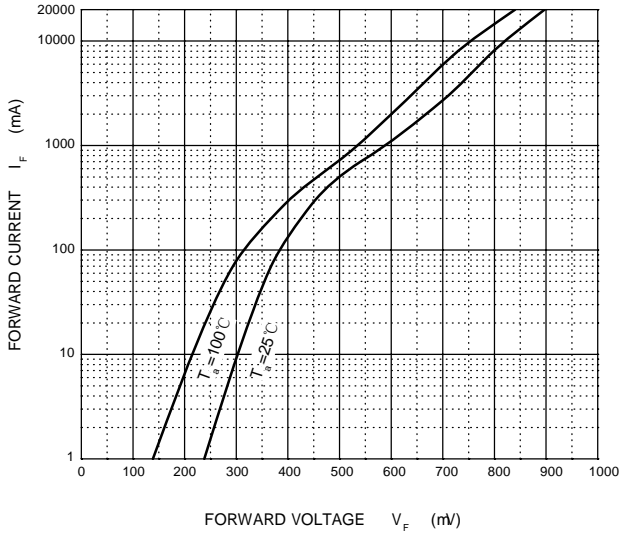
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	V _(BR)	I _R =1mA	200			V
Reverse current	I _R	V _R =100V			100	μA
Forward voltage	V _{F(1)}	I _F =10A T _j =25°C I _F =10A T _j =125°C			0.85 0.72	V
	V _{F(2)} *	I _F =20A			1.2	V

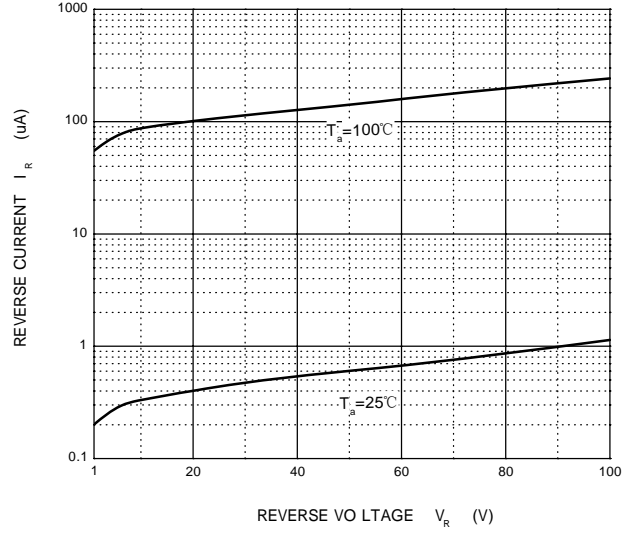
*Pulse test

Typical Characteristics

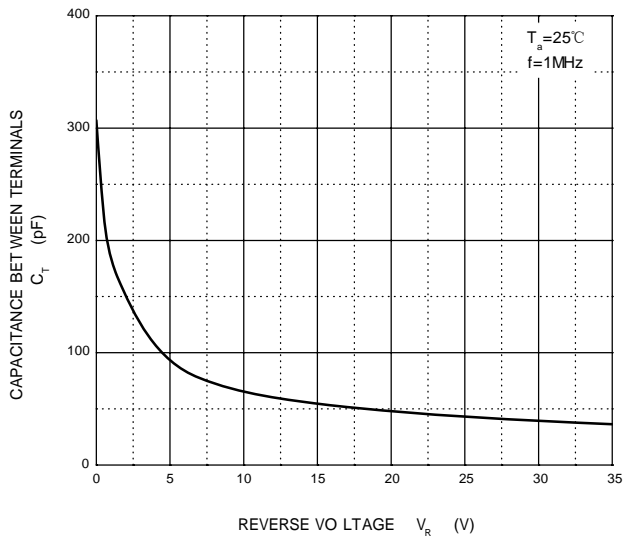
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

